



Sample &

Buv









SN74AVCH1T45

SCES598E-JULY 2004-REVISED MARCH 2016

SN74AVCH1T45 Single-Bit Dual-Supply Bus Transceiver With Configurable Level-Shifting, Voltage Translation, and 3-State Outputs

Features 1

- Available in the Texas Instruments NanoStar™ and NanoFree[™] Packages
- Control Inputs (DIR) VIH and VIL Levels Are Referenced to V_{CCA} Voltage
- Bus Hold on Data Inputs Eliminates the Need for External Pullup and Pulldown Resistors
- V_{CC} Isolation
- Fully Configurable Dual-Rail Design
- I/Os Are 4.6-V Tolerant
- Ioff Supports Partial-Power-Down Mode Operation
- Typical Max Data Rates
 - 500 Mbps (1.8-V to 3.3-V Translation)
 - 320 Mbps (<1.8-V to 3.3-V Translation)
 - 320 Mbps (Translate to 2.5 V or 1.8 V)
 - 280 Mbps (Translate to 1.5 V)
 - 240 Mbps (Translate to 1.2 V)
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Protection Exceeds JESD 22
 - Human-Body Model (A114-A): 2000 V
 - Machine Model (A115-A): 200 V
 - Charged-Device Model (C101): 1000 V

2 Applications

- Personal Electronics •
- Industrial
- Enterprise
- Telecommunications

3 Description

The SN74AVCH1T45 is a single-bit noninverting bus transceiver that uses two separate configurable power-supply rails. The A port is designed to track V_{CCA}, which accepts any supply voltage from 1.2 V to 3.6 V. The B port is designed to track V_{CCB}, which also accepts any supply voltage from 1.2 V to 3.6 V. This allows for universal low-voltage bidirectional translation between any of the 1.2-V, 1.5-V, 1.8-V, 2.5-V, and 3.3-V voltage nodes.

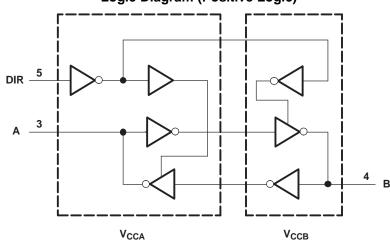
The SN74AVCH1T45 is designed for asynchronous communication between two data buses. The device transmits data from either the A bus to the B bus, or from the B bus to the A bus, depending upon the logic level at the direction-control (DIR) input.

The SN74AVCH1T45 is designed so that the DIR input is referenced to V_{CCA}.

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)
	SC70 (6)	2.00 mm × 1.25 mm
SN74AVCH1T45	SOT-23 (6)	2.90 mm × 1.60 mm
	DSBGA (6)	1.50 mm × 0.90 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.



Logic Diagram (Positive Logic)



1	Feat	ures 1
2	Арр	lications 1
3	Des	cription 1
4		sion History 2
5	Dese	cription (continued)
6		Configuration and Functions 3
7	Spe	cifications
	7.1	Absolute Maximum Ratings 4
	7.2	ESD Ratings 4
	7.3	Recommended Operating Conditions 4
	7.4	Thermal Information 5
	7.5	Electrical Characteristics
	7.6	Switching Characteristics, V _{CCA} = 1.2 V
	7.7	Switching Characteristics, V_{CCA} = 1.5 V ± 0.1 V 9
	7.8	Switching Characteristics, V_{CCA} = 1.8 V ± 0.15 V 10
	7.9	Switching Characteristics, V_{CCA} = 2.5 V ± 0.2 V 11
	7.10	Switching Characteristics, V_{CCA} = 3.3 V ± 0.3 V 12
	7.11	Operating Characteristics 13
	7.12	Typical Characteristics 14
8	Para	meter Measurement Information

9	Deta	iled Description	17
	9.1	Overview	17
	9.2	Functional Block Diagram	17
	9.3	Feature Description	17
	9.4	Device Functional Modes	18
10	Арр	lication and Implementation	18
	10.1	Application Information	18
	10.2	Typical Applications	18
11	Pow	ver Supply Recommendations	21
12	Lay	out	22
	12.1		
	12.2	Layout Example	22
13	Dev	ice and Documentation Support	23
	13.1	Documentation Support	23
	13.2	Community Resources	23
	13.3	Trademarks	23
	13.4	Electrostatic Discharge Caution	23
	13.5	Glossary	23
14	Mec	hanical, Packaging, and Orderable	
	Info	rmation	23

4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision D (January 2008) to Revision E

,	Added ESD Ratings table, Feature Description section, Device Functional Modes, Application and Implementation
	section, Power Supply Recommendations section, Layout section, Device and Documentation Support section, and
	Mechanical, Packaging, and Orderable Information section 1

www.ti.com

Page

2



5 Description (continued)

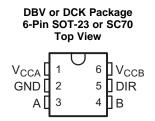
Active bus-hold circuitry holds unused or undriven inputs at a valid logic state. Use of pullup or pulldown resistors with the bus-hold circuitry is not recommended.

This device is fully specified for partial-power-down applications using I_{off}. The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device.

The V_{CC} isolation feature ensures that if either V_{CCA} or V_{CCB} is at GND, then the outputs are in the high-impedance state. The bus-hold circuitry on the powered-up side always stays active.

NanoFree package technology is a major breakthrough in IC packaging concepts, using the die as the package.

6 Pin Configuration and Functions





Pin Functions

PIN		I/O	DESCRIPTION		
NAME	NO.	1/0	DESCRIPTION		
A	3	I/O	Input/output A. Referenced to V _{CCA} .		
В	4	I/O	Input/output B. Referenced to V _{CCB} .		
DIR	5	I	Direction control signal. Referenced to V _{CCA} .		
V _{CCA}	1	—	A-port supply voltage. 1.2 V \leq V _{CCA} \leq 3.6 V		
V _{CCB}	6	—	B-port supply voltage. 1.2 V \leq V _{CCB} \leq 3.6 V.		
GND	2	—	Ground		

7 Specifications

7.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT	
Supply voltage	V_{CCA} and V_{CCB}	-0.5	4.6	V	
	I/O ports (A port)	-0.5	4.6		
Input voltage ⁽²⁾	I/O ports (B port)	-0.5	4.6	V	
	Control inputs	-0.5	4.6		
Voltage applied to any output in the high-impedance or power-off	A port	-0.5	-0.5 4.6 V -0.5 4.6 -0.5 4.6 -0.5 4.6	N/	
state ⁽²⁾	B port	-0.5	4.6	V	
Voltage applied to any output in the high or low state ⁽²⁾⁽³⁾	A port	-0.5	V _{CCA} + 0.5	N/	
voltage applied to any output in the high of low state	B port	-0.5	V _{CCB} + 0.5	V	
Input clamp current	V ₁ < 0		-50	mA	
Output clamp current	V _O < 0		-50	mA	
Continuous output current			±50	mA	
Continuous through current	V _{CCA} , V _{CCB} , or GND		±100	mA	
Junction temperature, T _J	+	-40	150	°C	
Storage temperature, T _{stg}		-65	150	°C	

(1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) The input voltage and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.

(3) The output positive-voltage rating may be exceeded up to 4.6 V maximum if the output current rating is observed.

7.2 ESD Ratings

			VALUE	UNIT
		Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000	
V _(ESD)	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1000	V
. ,		Machine model, per A115-A	±200	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

7.3 Recommended Operating Conditions

see (1)(2)(3)(4)(5)

				MIN	MAX	UNIT
V _{CCA}	Supply voltage			1.2	3.6	V
V _{CCB}	Supply voltage			1.2	3.6	V
			V _{CCI} = 1.2 V to 1.95 V	$V_{CCI} \times 0.65$		
V _{IH} High-level	High-level input voltage ⁽¹⁾	Data inputs ⁽⁴⁾	V_{CCI} = 1.95 V to 2.7 V	1.6		V
			V_{CCI} = 2.7 V to 3.6 V	2		
			V_{CCI} = 1.2 V to 1.95 V		$V_{CCI} \times 0.35$	
VIL	Low-level input voltage ⁽¹⁾	Data inputs ⁽⁴⁾	V_{CCI} = 1.95 V to 2.7 V		0.7	V
			V_{CCI} = 2.7 V to 3.6 V		0.8	
			V _{CCI} = 1.2 V to 1.95 V	$V_{CCA} \times 0.65$		
VIH	High-level input voltage	DIR (referenced to V _{CCA}) ⁽⁵⁾	V_{CCI} = 1.95 V to 2.7 V	1.6		V
			V_{CCI} = 2.7 V to 3.6 V	2		

(1) V_{CCI} is the V_{CC} associated with the input port.

(2) V_{CCO} is the V_{CC} associated with the output port.

(3) All unused control inputs of the device must be held at V_{CCI} or GND to ensure proper device operation.

(4) For V_{CCI} values not specified in the data sheet, V_{IH} min = $V_{CCI} \times 0.7$ V, V_{IL} max = $V_{CCI} \times 0.3$ V.

(5) For V_{CCI} values not specified in the data sheet, V_{IH} min = $V_{CCA} \times 0.7 \text{ V}$, V_{IL} max = $V_{CCA} \times 0.3 \text{ V}$.

4 Submit Documentation Feedback



Recommended Operating Conditions (continued)

see (1)(2)(3)(4)(5)

				MIN	MAX	UNIT	
			V _{CCI} = 1.2 V to 1.95 V	Vc	_{CCA} × 0.35		
VIL	Low-level input voltage	DIR (referenced to V _{CCA}) ⁽⁵⁾	V_{CCI} = 1.95 V to 2.7 V		0.7	V	
			V_{CCI} = 2.7 V to 3.6 V		0.8		
VI	Input voltage	Control Inputs ⁽³⁾		0	3.6	V	
V	O_{1}	Active state		0	V _{CCO}	V	
Vo	Output voltage ⁽²⁾	3-state		0	3.6	V	
			V _{CCO} = 1.2 V		-3		
			$V_{CCO} = 1.4 \text{ V to } 1.6 \text{ V}$		-6		
I _{OH}	High-level output current		$V_{CCO} = 1.65$ V to 1.95 V		-8	mA	
I _{OH}			V_{CCO} = 2.3 V to 2.7 V		-9		
			$V_{CCO} = 3 V \text{ to } 3.6 V$	$V_{CCA} \times 0.35$ 0.7 0.6 0 0 3.6 0 0 -3	-12		
			V _{CCO} = 1.2 V		3		
			$V_{CCO} = 1.4 \text{ V to } 1.6 \text{ V}$		6		
I _{OL}	Low-level output current		V_{CCO} = 1.65 V to 1.95 V		8	mA	
			V_{CCO} = 2.3 V to 2.7 V		9		
			$V_{CCO} = 3 V \text{ to } 3.6 V$		12	1	
Δt/Δv	Input transition rise or fall rate	e			5	ns/V	
T _A	Operating free-air temperatur	re		-40	85	°C	

7.4 Thermal Information

		SN74AVCH1T45				
	THERMAL METRIC ⁽¹⁾	DBV (SOT-23)	DCK (SC70)	YZP (DSBGA)	UNIT	
		6 PINS	6 PINS	6 PINS		
R _{θJA}	Junction-to-ambient thermal resistance ⁽²⁾	24.3	290.7	130	°C/W	
R _{0JC(top)}	Junction-to-case (top) thermal resistance	174.7	97	54	°C/W	
$R_{\theta JB}$	Junction-to-board thermal resistance	92.4	99.2	51	°C/W	
Ψ_{JT}	Junction-to-top characterization parameter	61.1	2.1	1	°C/W	
ψ_{JB}	Junction-to-board characterization parameter	92	98.4	50	°C/W	

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report, SPRA953.

(2) The package thermal impedance is calculated in accordance with JESD 51-7.

SN74AVCH1T45

SCES598E -JULY 2004-REVISED MARCH 2016



KAS

7.5 Electrical Characteristics

All typical limits apply over $T_A = 25^{\circ}C$, and all maximum and minimum limits apply over $T_A = -40^{\circ}C$ to $85^{\circ}C$ (unless otherwise noted). (1) (2) (3) (4)

	PARAMETER	TEST	CONDITIONS	MIN	TYP	MAX	UNIT	
		$I_{OH} = -100 \ \mu A, \ V_I = V_{IH}$	$V_{CCA} = V_{CCB} = 1.2$ V to 3.6 V	V _{CCO} - 0.2 V				
		$I_{OH} = -3 \text{ mA}, \text{ V}_{I} = \text{ V}_{IH}$	$V_{CCA} = V_{CCB} = 1.2 V$		0.95			
	High-level output	$I_{OH} = -6 \text{ mA}, \text{ V}_{I} = \text{ V}_{IH}$	$V_{CCA} = V_{CCB} = 1.4 V$	1.05			V	
V _{OH}	voltage ⁽¹⁾	$I_{OH} = -8 \text{ mA}, \text{ V}_{I} = \text{V}_{IH}$	$V_{CCA} = V_{CCB} = 1.65 V$	1.2			v	
		$I_{OH} = -9 \text{ mA}, \text{ V}_{I} = \text{V}_{IH}$	$V_{CCA} = V_{CCB} = 2.3 V$	1.75				
		$I_{OH} = -12 \text{ mA}, V_I = V_{IH}$	$V_{CCA} = V_{CCB} = 3 V$	2.3				
		$I_{OL}=100~\mu\text{A},~V_{I}{=}~V_{IL}$	$V_{CCA} = V_{CCB} = 1.2$ V to 3.6 V			0.2		
		$I_{OL} = 3 \text{ mA}, V_I = V_{IL}$	$V_{CCA} = V_{CCB} = 1.2 V$		0.15			
V	Low-level output	$I_{OL} = 6 \text{ mA}, V_I = V_{IL}$	$V_{CCA} = V_{CCB} = 1.4 V$			0.35	V	
V _{OL}	voltage	$I_{OL} = 8 \text{ mA}, V_I = V_{IL}$	$V_{CCA} = V_{CCB} = 1.65 V$			0.45	v	
		$I_{OL} = 9 \text{ mA}, V_I = V_{IL}$	$V_{CCA} = V_{CCB} = 2.3 V$			0.55		
		I_{OL} = 12 mA, V_{I} = V_{IL}	$V_{CCA} = V_{CCB} = 3 V$			0.7		
l _l	Control Input (DIR)	$V_I = V_{CCA}$ or GND	$V_{CCA} = V_{CCB} = 1.2$ V to 3.6 V		±0.025	±1	μA	
		V _I = 0.42 V	$V_{CCA} = V_{CCB} = 1.2 V$		25			
	Bus-hold low	V _I = 0.49 V	$V_{CCA} = V_{CCB} = 1.4 V$	15				
I _{BHL}	sustaining current ⁽⁵⁾	V _I = 0.58 V	$V_{CCA} = V_{CCB} = 1.65 V$	25		μA		
		V _I = 0.7 V	$V_{CCA} = V_{CCB} = 2.3 V$	45				
		V _I = 0.8 V	8 V V _{CCA} = V _{CCB} = 3.3 V 100					
		V _I = 0.78 V	$V_{CCA} = V_{CCB} = 1.2 V$		-25			
	Bus-hold high	V _I = 0.91 V	$V_{CCA} = V_{CCB} = 1.4 V$	-15				
I _{BHH}	sustaining	V _I = 1.07 V	$V_{CCA} = V_{CCB} = 1.65 V$	-25			μA	
	current ^{(6)⁻}	V _I = 1.6 V	$V_{CCA} = V_{CCB} = 2.3 V$	$CCA = V_{CCB} = 2.3 \text{ V} -45$				
		V ₁ = 2 V	$V_{CCA} = V_{CCB} = 3.3 V$	-100				
				$V_{CCA} = V_{CCB} = 1.2 V$		50		
	Bus-hold low		$V_{CCA} = V_{CCB} = 1.6 V$	125				
I _{BHLO}	overdrive	$V_I = 0$ to V_{CC}	$V_{CCA} = V_{CCB} = 1.95 V$	200			μA	
	current ⁽³⁾		$V_{CCA} = V_{CCB} = 2.7 V$	300			1	
			$V_{CCA} = V_{CCB} = 3.6 V$	500				
			$V_{CCA} = V_{CCB} = 1.2 V$		-50			
	Bus-hold high		$V_{CCA} = V_{CCB} = 1.6 V$	-125			1	
I _{BHHO}	overdrive	$V_I = 0$ to V_{CC}	$V_{CCA} = V_{CCB} = 1.95 V$	-200			μA	
	current ⁽⁴⁾		$V_{CCA} = V_{CCB} = 2.7 V$	-300				
			$V_{CCA} = V_{CCB} = 3.6 V$	-500				
1	Input and output	$V_1 = 0 V \text{ to } 3.6 V,$	$ \begin{array}{c} V_{CCA} = 0 \ V, \\ V_{CCB} = 0 \ V \ to \ 3.6 \ V \end{array} \ \ \ A \ \ Port $		±0.1	±5		
l _{off}	Power-off leakge current	$V_{O}=0$ V to 3.6 V	$V_{CCA} = 0 V \text{ to } 3.6 V, \\ V_{CCB} = 0 V $ B Port		±0.1	±5	μA	

(1)

(2)

(3)

(4)

- V_{CCO} is the V_{CC} associated with the output port. V_{CCI} is the V_{CC} associated with the input port. An external driver must source at least I_{BHLO} to switch this node from low to high. An external driver must sink at least I_{BHHO} to switch this node from high to low. The bus-hold circuit can sink at least the minimum low sustaining current at V_{IL} max. I_{BHL} should be measured after lowering V_{IN} to GND and then raising it to V_{IC} max. (5) and then raising it to V_{IL} max.
- The bus-hold circuit can source at least the minimum high sustaining current at VIH min. IBHH should be measured after raising VIN to (6) V_{CC} and then lowering it to V_{IH} min.



Electrical Characteristics (continued)

All typical limits apply over $T_A = 25^{\circ}C$, and all maximum and minimum limits apply over $T_A = -40^{\circ}C$ to 85°C (unless otherwise noted).⁽¹⁾⁽²⁾⁽³⁾⁽⁴⁾

	PARAMETER	PARAMETER TEST CONDITIONS			MIN	TYP	MAX	UNIT
	Off-state output	$V_{I} = V_{CCI}$ or GND,	V _{CCA} = 0 V, V _{CCB} = 3.6 V	A Port		±0.5	±5	
I _{OZ}	current ⁽⁷⁾	$V_0 = V_{CCO}$ or GND	$\begin{array}{l} V_{\mathrm{CCA}}=3.6 \ V, \\ V_{\mathrm{CCB}}=0 \ V \end{array}$	B port		±0.5	±5	μA
			$V_{CCA} = V_{CCB} = 1.2 V$	to 3.6 V			10	
I _{CCA}	Supply current A port	$V_I = V_{CCI}$ or GND, $I_O = 0$	$V_{CCA} = 0 V, V_{CCB} = 3$	3.6 V			-2	μA
	pon		$V_{CCA} = 3.6 \text{ V}, V_{CCB} = 0 \text{ V}$				10	
			$V_{CCA} = V_{CCB} = 1.2$ V to 3.6 V				10	
I _{CCB}	Supply current B	$V_I = V_{CCI}$ or GND, $I_O = 0$	$V_{CCA} = 0 V, V_{CCB} = 3.6 V$				10	μA
	pon		$V_{CCA} = 3.6 V, V_{CCB} = 0 V$				-2	
I _{CCA} + I _{CCB}	Combined supply current	$V_{I} = V_{CCI}$ or GND, $I_{O} = 0$	$V_{CCA} = V_{CCB} = 1.2 \text{ V to } 3.6 \text{ V}$				20	μΑ
Ci	Input capacitance control pin (DIR)	V ₁ = 3.3 V or GND	$V_{CCA} = V_{CCB} = 3.3 V$			2.5		pF
C _{io}	Input and output capacitance A or B port	$V_{O} = 3.3 V \text{ or GND}$	$V_{CCA} = V_{CCB} = 3.3 V$			6		pF

(7) For I/O ports, the parameter I_{OZ} includes the input leakage current.

SN74AVCH1T45

SCES598E – JULY 2004 – REVISED MARCH 2016

Texas Instruments

www.ti.com

7.6 Switching Characteristics, V_{CCA} = 1.2 V

 T_A = 25°C (see Figure 11).

	PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	MIN	ТҮР	МАХ	UNIT
				V _{CCB} = 1.2 V		3.3		
	Propagation delay time:			V _{CCB} = 1.5 V		2.7		
t _{PLH} , t _{PHL}	low-to-high-level output and	А	В	V _{CCB} = 1.8 V		2.4		ns
PHL	high-to-low level output			V _{CCB} = 2.5 V		2.3		
				V _{CCB} = 3.3 V		2.4		
				V _{CCB} = 1.2 V		3.3		
	Propagation delay time:			V _{CCB} = 1.5 V		3.1		
t _{PLH} , t _{PHL}	low-to-high-level output and	В	А	V _{CCB} = 1.8 V		2.9		ns
PHL	high-to-low level output			V _{CCB} = 2.5 V		2.8		
				V _{CCB} = 3.3 V		2.7		
				V _{CCB} = 1.2 V		5.1		ns
	Enable time:	DIR	A	V _{CCB} = 1.5 V		5.2		
t _{PZH} ,	^{H,} to high level ⁽¹⁾ and			V _{CCB} = 1.8 V		5.3		
t _{PZL}				V _{CCB} = 2.5 V		5.2		
				V _{CCB} = 3.3 V		3.7		
		DIR	В	V _{CCB} = 1.2 V		5.3		ns
	Enable time:			V _{CCB} = 1.5 V		4.3		
t _{PZH} , t _{PZL}	to high level ⁽¹⁾ and			V _{CCB} = 1.8 V		4		
PZL	to low level ⁽¹⁾			V _{CCB} = 2.5 V		3.3		
				V _{CCB} = 3.3 V		3.7		
				V _{CCB} = 1.2 V		8.5		
	Disable time:			V _{CCB} = 1.5 V		6.9		
t _{PHZ} , t _{PLZ}	from high level and	DIR	А	V _{CCB} = 1.8 V		6.4		ns
PLZ	from low level			V _{CCB} = 2.5 V		5.5		
				V _{CCB} = 3.3 V		6.1		l .
				V _{CCB} = 1.2 V		8.3		
	Disable time:			V _{CCB} = 1.5 V		7.8		ns
t _{PHZ} , t _{PLZ}	from high level and	DIR	В	V _{CCB} = 1.8 V		7.7		
PLZ	from low level			V _{CCB} = 2.5 V		7.5		
				V _{CCB} = 3.3 V		5.9		

(1) The enable time is a calculated value, derived using the formula shown in *Enable Times*.

Copyright © 2004–2016, Texas Instruments Incorporated



7.7 Switching Characteristics, V_{CCA} = 1.5 V ± 0.1 V

All typical limits apply over $T_A = 25^{\circ}C$, and all maximum and minimum limits apply over $T_A = -40^{\circ}C$ to 85°C (unless otherwise noted) (see Figure 11).

	PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	MIN	ТҮР	МАХ	UNIT
				V _{CCB} = 1.2 V		2.9		
	Propagation delay time:			V _{CCB} = 1.5 V ± 0.1 V	0.7		5.6	
t _{PLH} , t _{PHL}	low-to-high-level output and	А	В	V _{CCB} = 1.8 V ± 0.15 V	0.6		4.2	ns
PHL	high-to-low level output			$V_{CCB} = 2.5 V \pm 0.2 V$	0.5		4.2	
				$V_{CCB} = 3.3 \text{ V} \pm 0.3 \text{ V}$	0.5		3.8	
				V _{CCB} = 1.2 V		2.6		
	Propagation delay time:			$V_{CCB} = 1.5 V \pm 0.1 V$	0.6		5.5	
t _{PLH} , t _{PHL}	low-to-high-level output and	В	А	$V_{CCB} = 1.8 \text{ V} \pm 0.15 \text{ V}$	0.4		5.3	ns
PHL	high-to-low level output			$V_{CCB} = 2.5 V \pm 0.2 V$	0.3		4.9	
				$V_{CCB} = 3.3 \text{ V} \pm 0.3 \text{ V}$	0.3		4.8	
			A	V _{CCB} = 1.2 V		3.8		ns
	Enable time: to high level ⁽¹⁾ and to low level ⁽¹⁾	DIR		$V_{CCB} = 1.5 V \pm 0.1 V$	1.6		6.7	
t _{PZH} , t _{PZL}				V _{CCB} = 1.8 V ± 0.15 V	1.5		6.8	
ΨZL				$V_{CCB} = 2.5 V \pm 0.2 V$	0.3		6.9	
				$V_{CCB} = 3.3 \text{ V} \pm 0.3 \text{ V}$	0.9		6.9	
	Enable time: to high leve! ⁽¹⁾ and	level ⁽¹⁾ and DIR		V _{CCB} = 1.2 V		5.1		ns
			В	$V_{CCB} = 1.5 V \pm 0.1 V$	1.8		8.1	
t _{PZH} , t _{PZL}				V _{CCB} = 1.8 V ± 0.15 V	1.6		7.1	
PZL	to low level ⁽¹⁾			$V_{CCB} = 2.5 V \pm 0.2 V$	1.1		4.7	
				$V_{CCB} = 3.3 \text{ V} \pm 0.3 \text{ V}$	1.4		4.5	
				V _{CCB} = 1.2 V		7.7		
	Disable time:			$V_{CCB} = 1.5 V \pm 0.1 V$			13.6	
t _{PHZ} , t _{PLZ}	from high level and	DIR	А	V _{CCB} = 1.8 V ± 0.15 V			12.4	ns
PLZ	from low level			$V_{CCB} = 2.5 V \pm 0.2 V$			9.6	
				$V_{CCB} = 3.3 \text{ V} \pm 0.3 \text{ V}$			9.3	
				V _{CCB} = 1.2 V		6.7		ns
	Disable time:			$V_{CCB} = 1.5 V \pm 0.1 V$			12.3	
t _{PHZ} , t _{PLZ}	from high level and	DIR	В	V _{CCB} = 1.8 V ± 0.15 V			12	
•PLZ	from low level			$V_{CCB} = 2.5 \text{ V} \pm 0.2 \text{ V}$			11.1	
				$V_{CCB} = 3.3 \text{ V} \pm 0.3 \text{ V}$			10.7	

SN74AVCH1T45

SCES598E – JULY 2004 – REVISED MARCH 2016

TEXAS INSTRUMENTS

www.ti.com

7.8 Switching Characteristics, V_{CCA} = 1.8 V ± 0.15 V

All typical limits apply over $T_A = 25^{\circ}C$, and all maximum and minimum limits apply over $T_A = -40^{\circ}C$ to $85^{\circ}C$ (unless otherwise noted) (see Figure 11).

	PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	MIN	ТҮР	MAX	UNIT
				V _{CCB} = 1.2 V		2.8		
	Propagation delay time:			$V_{CCB} = 1.5 V \pm 0.1 V$	0.6		5.3	
t _{PLH} , t	low-to-high-level output and	А	В	V _{CCB} = 1.8 V ± 0.15 V	0.5		5	ns
t _{PHL}	high-to-low level output			$V_{CCB} = 2.5 V \pm 0.2 V$	0.4		3.9	
				$V_{CCB} = 3.3 \text{ V} \pm 0.3 \text{ V}$	0.4		3.4	
				V _{CCB} = 1.2 V		2.3		
	Propagation delay time:			$V_{CCB} = 1.5 V \pm 0.1 V$	0.5		5.2	
t _{PLH} , t _{PHL}	low-to-high-level output and	В	А	V _{CCB} = 1.8 V ± 0.15 V	0.4		5	ns
PHL	high-to-low level output			$V_{CCB} = 2.5 V \pm 0.2 V$	0.3		4.6	
				$V_{CCB} = 3.3 \text{ V} \pm 0.3 \text{ V}$	0.2		4.4	
			A	V _{CCB} = 1.2 V		3.8		ns
t _{PZH} , t _{PZL}	Enable time: to high level ⁽¹⁾ and to low level ⁽¹⁾	DIR		$V_{CCB} = 1.5 V \pm 0.1 V$	1.6		5.9	
				V _{CCB} = 1.8 V ± 0.15 V	1.6		5.9	
				$V_{CCB} = 2.5 V \pm 0.2 V$	1.6		5.9	
				$V_{CCB} = 3.3 \text{ V} \pm 0.3 \text{ V}$	0.5		6	
	Enable time: to high level ⁽¹⁾ and DIR			V _{CCB} = 1.2 V		5		1
			$V_{CCB} = 1.5 V \pm 0.1 V$	1.8		7.7	1	
t _{PZH} , t _{PZL}		DIR	В	$V_{CCB} = 1.8 \text{ V} \pm 0.15 \text{ V}$	1.4		6.8	+
PZL	to low level ⁽¹⁾			$V_{CCB} = 2.5 \text{ V} \pm 0.2 \text{ V}$	1		4.4	
				$V_{CCB} = 3.3 \text{ V} \pm 0.3 \text{ V}$	1.4		4.3	
				V _{CCB} = 1.2 V		7.3		
	Disable time:			$V_{CCB} = 1.5 V \pm 0.1 V$			12.9	
t _{PHZ} , t _{PLZ}	from high level and	DIR	А	$V_{CCB} = 1.8 \text{ V} \pm 0.15 \text{ V}$			11.8	ns
PLZ	from low level			$V_{CCB} = 2.5 \text{ V} \pm 0.2 \text{ V}$			9	
				$V_{CCB} = 3.3 \text{ V} \pm 0.3 \text{ V}$			8.7	
				V _{CCB} = 1.2 V		6.5		ns
	Disable time:			$V_{CCB} = 1.5 V \pm 0.1 V$			11.2	
t _{PHZ} , t _{PLZ}	from high level and	DIR	В	V _{CCB} = 1.8 V ± 0.15 V			10.9	
"P"LZ	from low level			$V_{CCB} = 2.5 \text{ V} \pm 0.2 \text{ V}$			9.8	
				$V_{CCB} = 3.3 \text{ V} \pm 0.3 \text{ V}$			9.4	



7.9 Switching Characteristics, V_{CCA} = 2.5 V ± 0.2 V

All typical limits apply over $T_A = 25^{\circ}C$, and all maximum and minimum limits apply over $T_A = -40^{\circ}C$ to 85°C (unless otherwise noted) (see Figure 11).

	PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	MIN	ТҮР	МАХ	UNIT
				V _{CCB} = 1.2 V		2.6		
	Propagation delay time:			$V_{CCB} = 1.5 \text{ V} \pm 0.1 \text{ V}$	0.5		4.9	
t _{PLH} , t	low-to-high-level output and	А	В	V _{CCB} = 1.8 V ± 0.15 V	0.4		4.6	ns
t _{PHL}	high-to-low level output			$V_{CCB} = 2.5 V \pm 0.2 V$	0.3		3.4	
				$V_{CCB} = 3.3 \text{ V} \pm 0.3 \text{ V}$	0.3		3	
				V _{CCB} = 1.2 V		2.2		
	Propagation delay time:			$V_{CCB} = 1.5 V \pm 0.1 V$	0.4		4.2	
t _{PLH} , t _{PHL}	low-to-high-level output and	В	А	$V_{CCB} = 1.8 \text{ V} \pm 0.15 \text{ V}$	0.3		3.8	ns
PHL	high-to-low level output			$V_{CCB} = 2.5 \text{ V} \pm 0.2 \text{ V}$	0.2		3.4	
				V_{CCB} = 3.3 V ± 0.3 V	0.2		3.3	
t _{PZH} , t _{PZL}			A	V _{CCB} = 1.2 V		2.8		ns
	Enable time: to high level ⁽¹⁾ and to low level ⁽¹⁾	DIR		$V_{CCB} = 1.5 V \pm 0.1 V$	0.3		3.8	
				$V_{CCB} = 1.8 \text{ V} \pm 0.15 \text{ V}$	0.8		3.8	
				$V_{CCB} = 2.5 \text{ V} \pm 0.2 \text{ V}$	0.4		3.8	
				$V_{CCB} = 3.3 \text{ V} \pm 0.3 \text{ V}$	0.5		3.8	
	Enable time: to high leve $\binom{(1)}{(4)}$ and	level ⁽¹⁾ and DIR		V _{CCB} = 1.2 V		4.9		ns
			В	$V_{CCB} = 1.5 V \pm 0.1 V$	2		7.6	
t _{PZH} , t _{PZL}				$V_{CCB} = 1.8 \text{ V} \pm 0.15 \text{ V}$	1.5		6.5	
PZL	to low level ⁽¹⁾			$V_{CCB} = 2.5 \text{ V} \pm 0.2 \text{ V}$	0.6		4.1	
				$V_{CCB} = 3.3 \text{ V} \pm 0.3 \text{ V}$	1		4	
				V _{CCB} = 1.2 V		7.1		
	Disable time:			$V_{CCB} = 1.5 V \pm 0.1 V$			11.8	
t _{PHZ} , t _{PLZ}	from high level and	DIR	А	$V_{CCB} = 1.8 \text{ V} \pm 0.15 \text{ V}$			10.3	ns
PLZ	from low level			$V_{CCB} = 2.5 \text{ V} \pm 0.2 \text{ V}$			7.5	
				$V_{CCB} = 3.3 \text{ V} \pm 0.3 \text{ V}$			7.3	
				V _{CCB} = 1.2 V		5.4		
	Disable time:			$V_{CCB} = 1.5 V \pm 0.1 V$			8.6	ns
t _{PHZ} , t _{PLZ}	from high level and	DIR	В	V _{CCB} = 1.8 V ± 0.15 V			8.1	
•PLZ	from low level			$V_{CCB} = 2.5 \text{ V} \pm 0.2 \text{ V}$			7	
				$V_{CCB} = 3.3 \text{ V} \pm 0.3 \text{ V}$			6.6	

SN74AVCH1T45

SCES598E – JULY 2004 – REVISED MARCH 2016

TEXAS INSTRUMENTS

www.ti.com

7.10 Switching Characteristics, V_{CCA} = 3.3 V ± 0.3 V

All typical limits apply over $T_A = 25^{\circ}C$, and all maximum and minimum limits apply over $T_A = -40^{\circ}C$ to 85°C (unless otherwise noted) (see Figure 11).

	PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	MIN	ТҮР	МАХ	UNIT
				V _{CCB} = 1.2 V		2.6		
	Propagation delay time:			V _{CCB} = 1.5 V ± 0.1 V	0.4		4.7	
t _{PLH} , t	low-to-high-level output and	А	В	V _{CCB} = 1.8 V ± 0.15 V	0.3		4.4	ns
t _{PHL}	high-to-low level output			V _{CCB} = 2.5 V ± 0.2 V	0.2		3.3	
				$V_{CCB} = 3.3 \text{ V} \pm 0.3 \text{ V}$	0.2		2.8	
				V _{CCB} = 1.2 V		2.2		
	Propagation delay time:			$V_{CCB} = 1.5 V \pm 0.1 V$	0.4		3.8	
t _{PLH} , t _{PHL}	low-to-high-level output and	В	А	V _{CCB} = 1.8 V ± 0.15 V	0.3		3.4	ns
PHL	high-to-low level output			V _{CCB} = 2.5 V ± 0.2 V	0.2		3	
				$V_{CCB} = 3.3 \text{ V} \pm 0.3 \text{ V}$	0.1		2.8	
			A	V _{CCB} = 1.2 V		3.1		ns
t _{PZH} , t _{PZL}	Enable time: to high level ⁽¹⁾ and to low level ⁽¹⁾	DIR		V _{CCB} = 1.5 V ± 0.1 V	1.3		4.3	
				V _{CCB} = 1.8 V ± 0.15 V	1.3		4.3	
				V _{CCB} = 2.5 V ± 0.2 V	1.3		4.3	
				V _{CCB} = 3.3 V ± 0.3 V	1.3		4.3	
	Enable time: to high leve! ⁽¹⁾ and	DIR	В	V _{CCB} = 1.2 V		4		ns
				V _{CCB} = 1.5 V ± 0.1 V	0.7		7.4	
t _{PZH} , t _{PZL}				V _{CCB} = 1.8 V ± 0.15 V	0.6		6.5	
ΨZL	to low level ⁽¹⁾			$V_{CCB} = 2.5 V \pm 0.2 V$	0.7		4	
				$V_{CCB} = 3.3 \text{ V} \pm 0.3 \text{ V}$	1.5		3.9	
				V _{CCB} = 1.2 V		6.2		
	Disable time:			$V_{CCB} = 1.5 \text{ V} \pm 0.1 \text{ V}$			11.2	
t _{PHZ} , t _{PLZ}	from high level and	DIR	А	V _{CCB} = 1.8 V ± 0.15 V			9.9	ns
PLZ	from low level			$V_{CCB} = 2.5 \text{ V} \pm 0.2 \text{ V}$			7	
				$V_{CCB} = 3.3 \text{ V} \pm 0.3 \text{ V}$			6.7	
				V _{CCB} = 1.2 V		5.7		ns
	Disable time:			$V_{CCB} = 1.5 V \pm 0.1 V$			8.9	
t _{PHZ} , t _{PLZ}	from high level and	DIR	В	V _{CCB} = 1.8 V ± 0.15 V			8.5	
PLZ	from low level			$V_{CCB} = 2.5 V \pm 0.2 V$			7.2	
				V _{CCB} = 3.3 V ± 0.3 V			6.8	



7.11 Operating Characteristics

$T_A = 25^{\circ}C$

	PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CC	ONDITIONS	ТҮР	UNIT
					$V_{CCA} = V_{CCB} = 1.2 \text{ V}$	3	
				$C_{l} = 0 \text{ pF},$	$V_{CCA} = V_{CCB} = 1.5 V$	3	
		А	В	f = 10 MHz,	$V_{CCA} = V_{CCB} = 1.8 V$	3	pF
				$t_r = t_f = 1 \text{ ns}$	$V_{CCA} = V_{CCB} = 2.5 \text{ V}$	3	
C	Power dissipation capacitance per transceiver ⁽¹⁾				$V_{CCA} = V_{CCB} = 3.3 \text{ V}$	4	
C _{pdA}	port A				$V_{CCA} = V_{CCB} = 1.2 \text{ V}$	14	
			A	$C_{l} = 0 \text{ pF},$	$V_{CCA} = V_{CCB} = 1.5 V$	14	
		В		f = 10 MHz, $t_r = t_f = 1 \text{ ns}$	$V_{CCA} = V_{CCB} = 1.8 V$	14	pF
					$V_{CCA} = V_{CCB} = 2.5 V$	15	
					$V_{CCA} = V_{CCB} = 3.3 V$	16	
		A	В		$V_{CCA} = V_{CCB} = 1.2 V$	14	
				$C_{L} = 0 \text{ pF},$	$V_{CCA} = V_{CCB} = 1.5 V$	14	
				f = 10 MHz,	$V_{CCA} = V_{CCB} = 1.8 V$	14	pF
				$t_r = t_f = 1 \text{ ns}$	$V_{CCA} = V_{CCB} = 2.5 V$	15	
0	Power dissipation capacitance				$V_{CCA} = V_{CCB} = 3.3 V$	16	
C _{pdB}	per transceiver ⁽¹⁾ port B				$V_{CCA} = V_{CCB} = 1.2 V$	3	
	•			$C_{1} = 0 \text{ pF},$	$V_{CCA} = V_{CCB} = 1.5 V$	3	
		В	A	f = 10 MHz,	$V_{CCA} = V_{CCB} = 1.8 \text{ V}$	3	
				$t_r = t_f = 1 \text{ ns}$	$V_{CCA} = V_{CCB} = 2.5 V$	3	
					$V_{CCA} = V_{CCB} = 3.3 V$	4	

(1) See CMOS Power Consumption and Cpd Calculation, SCAA035.

SN74AVCH1T45

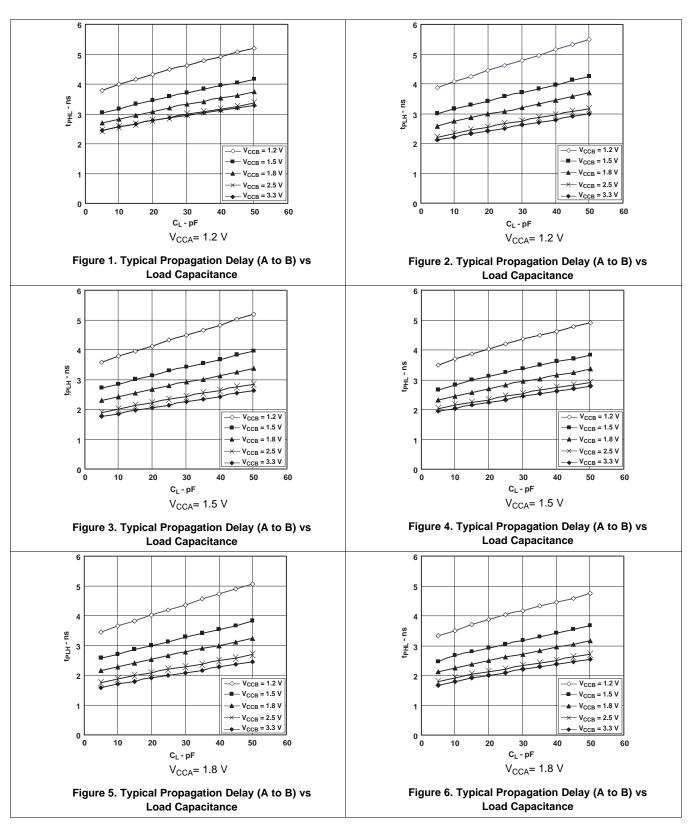
SCES598E -JULY 2004-REVISED MARCH 2016



www.ti.com

7.12 Typical Characteristics

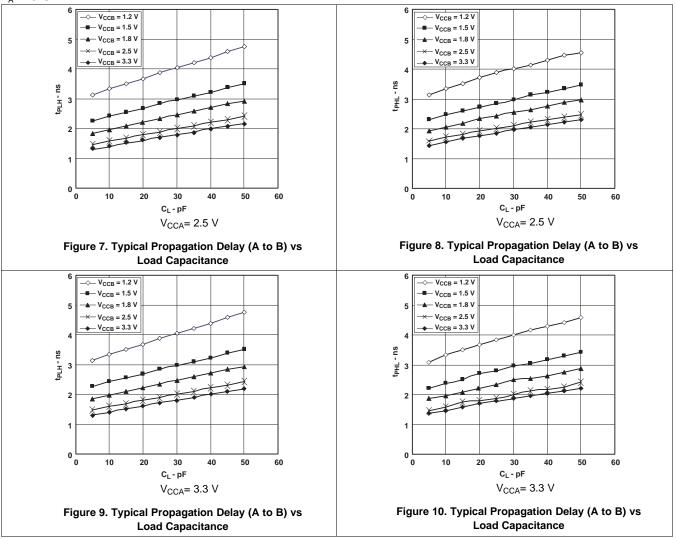
T_A= 25°C





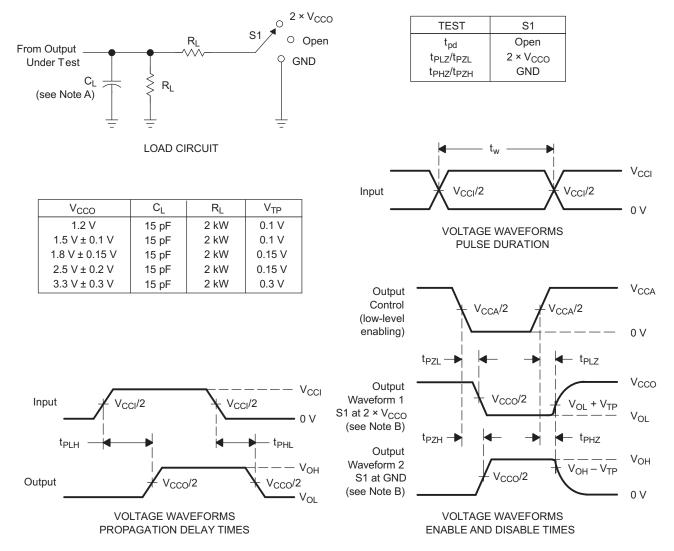
Typical Characteristics (continued)







8 Parameter Measurement Information



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR 10 MHz, $Z_0 = 50$ W, dv/dt ≥ 1 V/ns.
- D. The outputs are measured one at a time, with one transition per measurement.
- E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
- F. t_{PZL} and t_{PZH} are the same as t_{en} .
- G. t_{PLH} and t_{PHL} are the same as t_{pd} .
- H. V_{CCI} is the V_{CC} associated with the input port.
- I. V_{CCO} is the V_{CC} associated with the output port.

Figure 11. Load Circuit and Voltage Waveforms



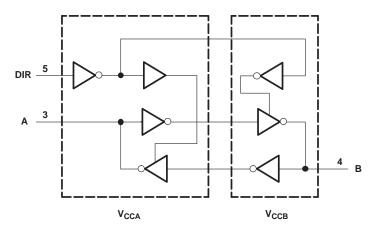
9

9.1 Overview

Detailed Description

The SN74AVCH1T45 is a single-bit, dual-supply, noninverting voltage level translator. Pins A and DIR are referenced to V_{CCA} , while pin B is referenced to V_{CCB} . Both the A port and B port can accept I/O voltages ranging from 1.2 V to 3.6 V. The high on DIR allows data transmission from Port A to Port B and a low on DIR allows data transmission from Port A to Port B and a low on DIR allows data transmission from Port A to Port B and A pplications (SCLA015), for more information.

9.2 Functional Block Diagram



9.3 Feature Description

9.3.1 Fully Configurable Dual-Rail Design

Both V_{CCA} and V_{CCB} can be supplied at any voltage from 1.2 V to 3.6 V, making the device suitable for translating between any of the voltage nodes (1.2 V, 1.8 V, 2.5 V and 3.3 V).

9.3.2 Supports High-Speed Translation

SN74AVCH1T45 can support high data rate applications, which can be calculated from the maximum propagation delay. This is also dependent on output load. For example, a 1.8-V to 3.3-V conversion yields a maximum data rate of 500 Mbps.

9.3.3 Partial-Power-Down Mode Operation

I_{off} circuitry disables the outputs, preventing damaging current backflow through the SN74AVCH1T45 when it is powered down. This can occur in applications where subsections of a system are powered down (partial-powerdown) to reduce power consumption.

9.3.4 Active Bus-Hold Circuitry

Active bus-hold circuitry holds unused or undriven data inputs at a valid logic state, which helps with board space savings and reduced component costs. Use of pullup or pulldown resistors with the bus-hold circuitry is not recommended. See applications report, *Bus-Hold Circuit* (SCLA015), for more information.

9.3.5 V_{CC} Isolation

The V_{CC} isolation feature ensures that if either V_{CCA} or V_{CCB} are at GND (or < 0.4 V), both ports will be in a highimpedance state (I_{OZ} as shown in *Electrical Characteristics*). This prevents false logic levels from being presented to either bus.

Copyright © 2004–2016, Texas Instruments Incorporated

SN74AVCH1T45

SCES598E – JULY 2004 – REVISED MARCH 2016

9.4 Device Functional Modes

Table 1 lists the functional modes of the SN74AVCH1T45.

Table	1. I	Function	Table
-------	------	----------	-------

DIR	OPERATION
L	B data to A bus
Н	A data to B bus

10 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

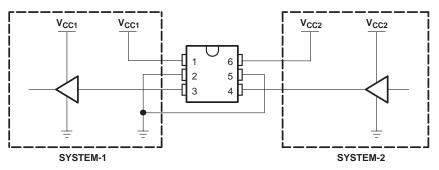
10.1 Application Information

The SN74AVCH1T45 device can be used in level-translation applications for interfacing devices or systems operating at different interface voltages with one another. The maximum data rate can be up to 500 Mbps when device translate signal from 1.8 V to 3.3 V.

10.2 Typical Applications

10.2.1 Unidirectional Logic Level-Shifting Application

Figure 12 shows an example of the SN74AVCH1T45 being used in a unidirectional logic level-shifting application.





PIN	NAME	FUNCTION	DESCRIPTION
1	V _{CCA}	V _{CC1}	SYSTEM-1 supply voltage (1.2 V to 3.6 V)
2	GND	GND	Device GND
3	А	OUT	Output level depends on V _{CC1} voltage.
4	В	IN	Input threshold value depends on V _{CC2} voltage.
5	DIR	DIR	GND (low level) determines B-port to A-port direction.
6	V _{CCB}	V _{CC2}	SYSTEM-2 supply voltage (1.2 V to 3.6 V)

18 Submit Documentation Feedback

Copyright © 2004–2016, Texas Instruments Incorporated

ISTRUMENTS

FXAS



10.2.1.1 Design Requirements

For this design example, use the parameters listed in Table 3.

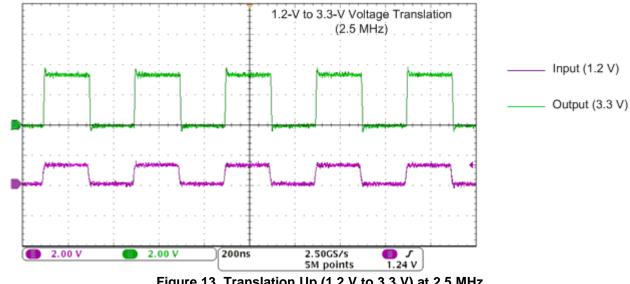
U U						
DESIGN PARAMETERS	EXAMPLE VALUES					
Input voltage	1.2 V to 3.6 V					
Output voltage	1.2 V to 3.6 V					

Table 3. Design Parameters

10.2.1.2 Detailed Design Procedure

To begin the design process, determine the following:

- Input voltage range
 - Use the supply voltage of the device that is driving the SN74AVCH1T45 device to determine the input voltage range. For a valid logic-high, the value must exceed the V_{IH} of the input port. For a valid logic low the value must be less than the V_{\parallel} of the input port.
- Output voltage range .
 - Use the supply voltage of the device that the SN74AVCH1T45 device is driving to determine the output voltage range.



10.2.1.3 Application Curve

Figure 13. Translation Up (1.2 V to 3.3 V) at 2.5 MHz



SN74AVCH1T45

SCES598E – JULY 2004 – REVISED MARCH 2016

10.2.2 Bidirectional Logic Level-Shifting Application

Figure 14 shows the SN74AVCH1T45 being used in a bidirectional logic level-shifting application. Because the SN74AVCH1T45 does not have an output-enable (OE) pin, the system designer should take precautions to avoid bus contention between SYSTEM-1 and SYSTEM-2 when changing directions.

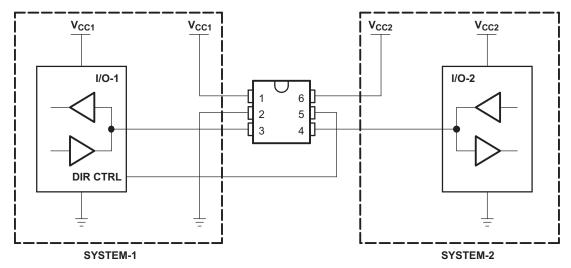


Figure 14. Bidirectional Logic Level-Shifting Application Diagram

The following table shows data transmission from SYSTEM-1 to SYSTEM-2 and then from SYSTEM-2 to SYSTEM-1.

Table 4. Data Transmission: SYSTEM-	and SYSTEM-2
-------------------------------------	--------------

STATE	DIR CTRL	I/O-1	I/O-2	DESCRIPTION
1	Н	Out	In	SYSTEM-1 data to SYSTEM-2
2	Н	Hi-Z	Hi-Z	SYSTEM-2 is getting ready to send data to SYSTEM-1. I/O-1 and I/O-2 are disabled.
3	L	Hi-Z	Hi-Z	DIR bit is flipped. I/O-1 and I/O-2 still are disabled.
4	L	In	Out	SYSTEM-2 data to SYSTEM-1

10.2.2.1 Design Requirements

Refer to Design Requirements found in Unidirectional Logic Level-Shifting Application.

10.2.2.2 Detailed Design Procedure

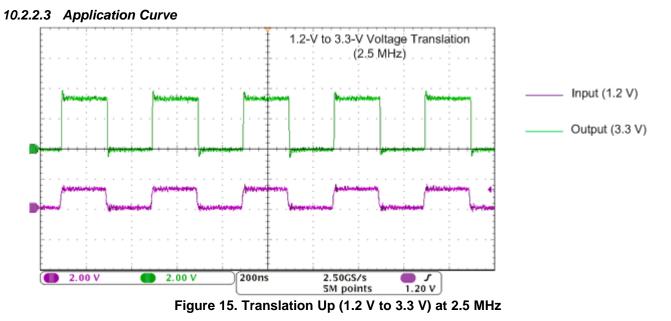
10.2.2.2.1 Enable Times

Calculate the enable times for the SN74AVCH1T45 using the following formulas:

- t_{PZH} (DIR to A) = t_{PLZ} (DIR to B) + t_{PLH} (B to A)
- t_{PZI} (DIR to A) = t_{PHZ} (DIR to B) + t_{PHI} (B to A)
- t_{PZH} (DIR to B) = t_{PLZ} (DIR to A) + t_{PLH} (A to B)
- t_{PZL} (DIR to B) = t_{PHZ} (DIR to A) + t_{PHL} (A to B)

In a bidirectional application, these enable times provide the maximum delay from the time the DIR bit is switched until an output is expected. For example, if the SN74AVCH1T45 initially is transmitting from A to B, then the DIR bit is switched; the B port of the device must be disabled before presenting it with an input. After the B port has been disabled, an input signal applied to it appears on the corresponding A port after the specified propagation delay.





11 Power Supply Recommendations

A proper power-up sequence must be followed to avoid excessive supply current, bus contention, oscillations, or other anomalies. To guard against such power-up problems, take the following precautions:

- 1. Connect ground before any supply voltage is applied.
- 2. Power up V_{CCA}.
- 3. V_{CCB} can be ramped up along with or after V_{CCA} .

V _{CCB}		UNIT					
	0 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V	UNIT
0 V	0	<0.5	<0.5	<0.5	<0.5	<0.5	
1.2 V	<0.5	<1	<1	<1	<1	1	
1.5 V	<0.5	<1	<1	<1	<1	1	
1.8 V	<0.5	<1	<1	<1	<1	<1	μA
2.5 V	<0.5	1	<1	<1	<1	<1	
3.3 V	<0.5	1	<1	<1	<1	<1	

Table 5. Typical Total Static Power Consumption (I_{CCA} + I_{CCB})

SN74AVCH1T45 SCES598E – JULY 2004–REVISED MARCH 2016



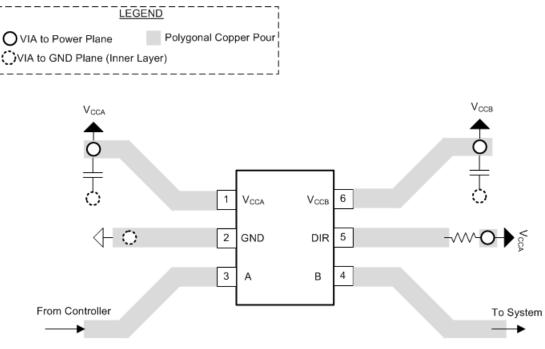
12 Layout

12.1 Layout Guidelines

To ensure reliability of the device, TI recommends following common printed-circuit board layout guidelines.

- Bypass capacitors should be used on power supplies.
- Short trace lengths should be used to avoid excessive loading.
- Placing pads on the signal paths for loading capacitors or pullup resistors to help adjust rise and fall times of signals depending on the system requirements.

12.2 Layout Example







13 Device and Documentation Support

13.1 Documentation Support

13.1.1 Related Documentation

For related documentation see the following:

- Designing with SN74LVCXT245 and SN74LVCHXT245 Family of Direction Controlled Voltage Translators/Level-Shifters, SLVA746
- Bus-Hold Circuit, SCLA015
- AVC Logic Family Technology and Applications, SCEA006

13.2 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E[™] Online Community *TI's Engineer-to-Engineer (E2E) Community.* Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support TI's Design Support Quickly find helpful E2E forums along with design support tools and contact information for technical support.

13.3 Trademarks

NanoStar, NanoFree, E2E are trademarks of Texas Instruments. All other trademarks are the property of their respective owners.

13.4 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

13.5 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

14 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



10-Dec-2020

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
74AVCH1T45DBVRE4	ACTIVE	SOT-23	DBV	6	3000	RoHS & Green	(6) NIPDAU	Level-1-260C-UNLIM	-40 to 85	(ET1F, ET1R)	Samples
74AVCH1T45DBVRG4	ACTIVE	SOT-23	DBV	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	(ET1F, ET1R)	Samples
74AVCH1T45DBVTG4	ACTIVE	SOT-23	DBV	6	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	(ET1F, ET1R)	Samples
74AVCH1T45DCKRE4	ACTIVE	SC70	DCK	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	(TFF, TFR)	Samples
74AVCH1T45DCKRG4	ACTIVE	SC70	DCK	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	(TFF, TFR)	Samples
74AVCH1T45DCKTG4	ACTIVE	SC70	DCK	6	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	(TFF, TFR)	Samples
SN74AVCH1T45DBVR	ACTIVE	SOT-23	DBV	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	(ET1F, ET1R)	Samples
SN74AVCH1T45DBVT	ACTIVE	SOT-23	DBV	6	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	(ET1F, ET1R)	Samples
SN74AVCH1T45DCKR	ACTIVE	SC70	DCK	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	(TFF, TFR)	Samples
SN74AVCH1T45DCKT	ACTIVE	SC70	DCK	6	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	(TFF, TFR)	Samples
SN74AVCH1T45YZPR	ACTIVE	DSBGA	YZP	6	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 85	(TE2, TE7, TEN)	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.



10-Dec-2020

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

PACKAGE MATERIALS INFORMATION

www.ti.com

Texas Instruments

TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74AVCH1T45DBVR	SOT-23	DBV	6	3000	180.0	8.4	3.23	3.17	1.37	4.0	8.0	Q3
SN74AVCH1T45DBVT	SOT-23	DBV	6	250	180.0	8.4	3.23	3.17	1.37	4.0	8.0	Q3
SN74AVCH1T45DCKR	SC70	DCK	6	3000	180.0	8.4	2.41	2.41	1.2	4.0	8.0	Q3
SN74AVCH1T45DCKT	SC70	DCK	6	250	180.0	8.4	2.41	2.41	1.2	4.0	8.0	Q3
SN74AVCH1T45YZPR	DSBGA	YZP	6	3000	178.0	9.2	1.02	1.52	0.63	4.0	8.0	Q1

Texas Instruments

www.ti.com

PACKAGE MATERIALS INFORMATION

18-Jan-2020



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74AVCH1T45DBVR	SOT-23	DBV	6	3000	202.0	201.0	28.0
SN74AVCH1T45DBVT	SOT-23	DBV	6	250	202.0	201.0	28.0
SN74AVCH1T45DCKR	SC70	DCK	6	3000	202.0	201.0	28.0
SN74AVCH1T45DCKT	SC70	DCK	6	250	202.0	201.0	28.0
SN74AVCH1T45YZPR	DSBGA	YZP	6	3000	220.0	220.0	35.0

DBV0006A



PACKAGE OUTLINE

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.2. This drawing is subject to change without notice.3. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.

- 4. Leads 1,2,3 may be wider than leads 4,5,6 for package orientation. 5. Refernce JEDEC MO-178.



DBV0006A

EXAMPLE BOARD LAYOUT

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



DBV0006A

EXAMPLE STENCIL DESIGN

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

9. Board assembly site may have different recommendations for stencil design.



YZP0006



PACKAGE OUTLINE

DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



NOTES:

NanoFree Is a trademark of Texas Instruments.

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice.
- 3. NanoFree[™] package configuration.



YZP0006

EXAMPLE BOARD LAYOUT

DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



NOTES: (continued)

4. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SBVA017 (www.ti.com/lit/sbva017).



YZP0006

EXAMPLE STENCIL DESIGN

DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



NOTES: (continued)

5. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.



DCK (R-PDSO-G6)

PLASTIC SMALL-OUTLINE PACKAGE



- NOTES: A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
 - D. Falls within JEDEC MO-203 variation AB.



LAND PATTERN DATA



NOTES:

- A. All linear dimensions are in millimeters.B. This drawing is subject to change without notice.
- C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
- D. Publication IPC-7351 is recommended for alternate designs.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.



IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATASHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, or other requirements. These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale (www.ti.com/legal/termsofsale.html) or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products.

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2020, Texas Instruments Incorporated